



#### **60V N-Channel Enhancement Mode MOSFET**

Voltage 60 V Current 250mA

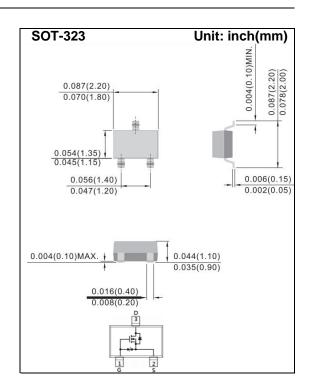
#### **Features**

- RDS(ON), VGS@10V, ID@300mA<5Ω
- RDS(ON), VGS@5V, ID@50mA<7.5Ω</li>
- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

Case: SOT-323 Package

Terminals: Solderable per MIL-STD-750, Method 2026



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	250	mA
Pulsed Drain Current		I <sub>DM</sub>	1000	mA
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	350	mW
	Derate above 25°C		2.8	mW/°C
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C
Typical Thermal Resistance - Junction to Ambient (Note 3)		$R_{ heta JA}$	357	°C/W





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	60	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	2.0	2.49	3.0	V		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =300mA	-	2.0	5	Ω		
		V <sub>GS</sub> =5V,I <sub>D</sub> =50mA	-	3.6	7.5			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	uA		
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 0.5	uA		
Dynamic (Note 4)								
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =300mA, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	1.3	-	nC		
Gate-Source Charge	$Q_gs$		-	0.6	-			
Gate-Drain Charge	$Q_{gd}$		-	0.2	-			
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	22	-	pF ns		
Output Capacitance	Coss		-	12	-			
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	1.7	-			
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =10V, $I_{D}$ =300mA, $V_{GS}$ =10V, $R_{G}$ =10 $\Omega$ (Note 1,2)	-	2.9	-			
Turn-On Rise Time	tr		-	1.8	-			
Turn-Off Delay Time	td <sub>(off)</sub>		-	5.6	-			
Turn-Off Fall Time	tf		-	1.9	-			
Drain-Source Diode								
Maximum Continuous Drain-Source				-	300	mA		
Diode Forward Current	I <sub>S</sub>							
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =300mA, V <sub>GS</sub> =0V	-	0.92	1.5	V		

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper
- 4. Guaranteed by design, not subject to production testing





#### **TYPICAL CHARACTERISTIC CURVES**

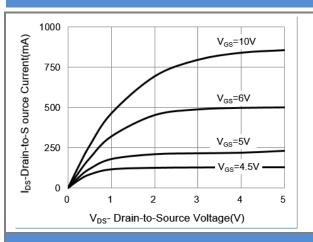
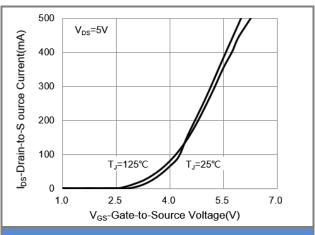


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

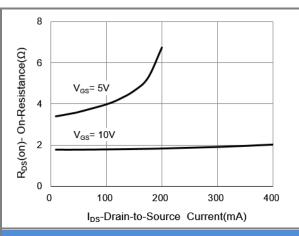


Fig.3 On-Resistance vs. Drain Current

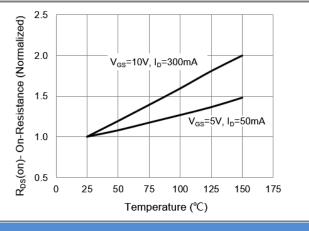


Fig.4 On-Resistance vs. Junction temperature

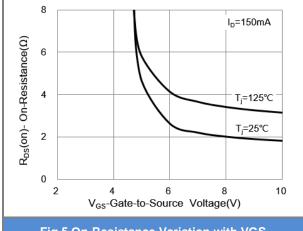


Fig.5 On-Resistance Variation with VGS.

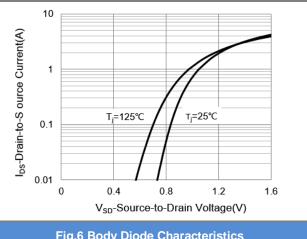


Fig.6 Body Diode Characteristics





#### **TYPICAL CHARACTERISTIC CURVES**

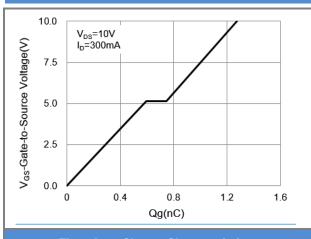


Fig.7 Gate-Charge Characteristics

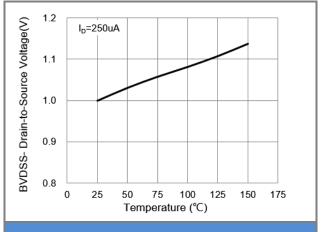


Fig.8 Breakdown Voltage Variation vs. Temperature

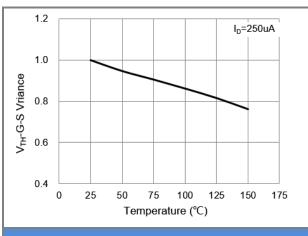


Fig.9 Threshold Voltage Variation with Temperature.

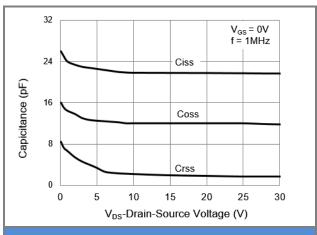


Fig.10 Capacitance vs. Drain-Source Voltage.

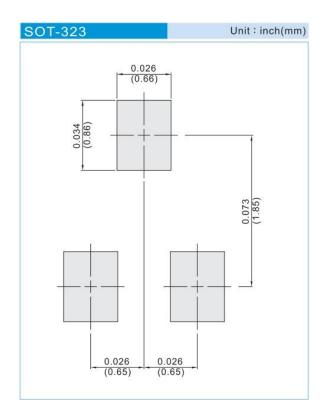




#### PART NO PACKING CODE VERSION

PART NO PACKING CODE	Package Type	Packing Type	Marking	Version
PJC7002H_R1_00001	SOT-323	3K pcs / 7" reel	C2H	Halogen free
PJC7002H_R2_00001	SOT-323	12K pcs / 13" reel	C2H	Halogen free

### **MOUNTING PAD LAYOUT**







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